September 2013



FNA41060 / FNA41060B2

Motion SPM® 45 Series

Features

- UL Certified No. E209204
- 600 V, 10 A 3 Phase IGBT Inverter Including Control ICs for Gate Drive and Protections
- Easy PCB Layout Thanks to The Built In Bootstrap Diodes and The Dedicated Vs Pins
- Three Separate Open Emitter Pins from Low Side IGBTs for Three Leg Current Sensing
- Single Grounded Power Supply with Bootstrap Operations
- Built In NTC Thermistor for Over Temperature Monitoring
- · Isolation Rating of 2000 Vrms / min.

Applications

· Motion Control - Home Appliance / Industrial Motor

Related Resources

- AN 9070 : Motion SPM® 45 Series Users Guide
- AN 9071: Motion SPM® 45 Series Thermal Performance Information
- AN 9072 : Motion SPM® 45 Series Mounting Guidance
- RD 344 : Reference Design (Three Shunt Solution)
- RD 345 : Reference Design (One Shunt Solution)

General Description

FNA41060 / FNA41060B2 Is A Motion SPM® 45 Series that Fairchild Has Newly Developed to Provide A Very Compact and High Performance Inverter Solution for AC Motor Drives in Low - Power Applications Such as Air Conditioners and Refrigerators. It Combines Low - Loss Short - Circuit Rated IGBTs and Optimized Gate Drivers in A Fully Isolated Package to Deliver A Simple and Robust Design. The System Reliability Is Further Enhanced by The Built - In NTC for Temperature Monitoring, Integrated Under - Voltage Lock - Out Function for Both High and Low Side, and An Over - Current Protection Input. Three Separate Open - Emitter Pins for Low Side IGBTs Make Three Leg Current Sensing Possible. Built - In Bootstrap Diodes and Dedicated VS Pins Make PCB Layout Easy.

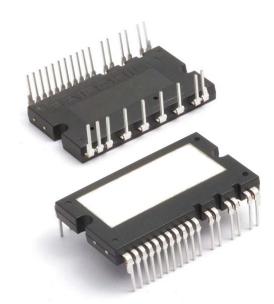


Figure 1. Package Overview

Package Marking and Ordering Information

Device Marking	Device	Package	Packing Type	Reel Size	Tape Width	Quantity
FNA41060	FNA41060	SPMAA - A26	RAIL	-	-	12
FNA41060B2	FNA41060B2	SPMAA - C26	RAIL	-	-	12

Integrated Power Functions

• 600 V -10 A IGBT inverter for three - phase DC / AC power conversion (Please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high side IGBTs: Gate drive circuit, High voltage isolated high speed level shifting Control circuit under - voltage (UV) protection
- For inverter low side IGBTs: Gate drive circuit, Short circuit protection (SC)
 Control supply circuit under voltage (UV) protection
- Fault signaling: Corresponding to UV (low side supply) and SC faults
- Input interface: Active high interface, schmitt trigger input, can work with 3.3 / 5 V logic

Pin Configuration

Top View

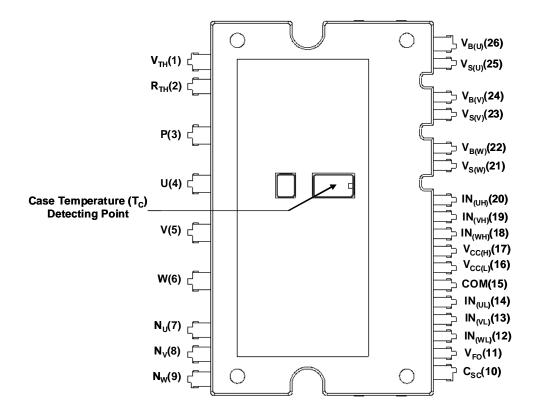
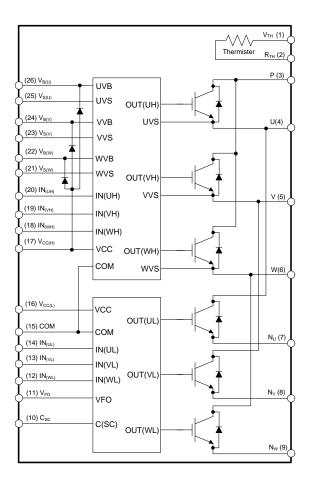


Figure 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	V_{TH}	Thermistor Bias Voltage
2	R _{TH}	Series Resistor for the Use of Thermistor (Temperature Detection)
3	Р	Positive DC - Link Input
4	U	Output for U Phase
5	V	Output for V Phase
6	W	Output for W Phase
7	N _U	Negative DC - Link Input for U Phase
8	N _V	Negative DC - Link Input for V Phase
9	N _W	Negative DC - Link Input for W Phase
10	C _{SC}	Capacitor (Low - Pass Filter) for Short - Current Detection Input
11	V _{FO}	Fault Output
12	IN _(WL)	Signal Input for Low - Side W Phase
13	IN _(VL)	Signal Input for Low - Side V Phase
14	IN _(UL)	Signal Input for Low - Side U Phase
15	СОМ	Common Supply Ground
16	V _{CC(L)}	Low - Side Common Bias Voltage for IC and IGBTs Driving
17	V _{CC(H)}	High - Side Common Bias Voltage for IC and IGBTs Driving
18	IN _(WH)	Signal Input for High - Side W Phase
19	IN _(VH)	Signal Input for High - Side V Phase
20	IN _(UH)	Signal Input for High - Side U Phase
21	V _{S(W)}	High - Side Bias Voltage Ground for W Phase IGBT Driving
22	V _{B(W)}	High - Side Bias Voltage for W Phase IGBT Driving
23	V _{S(V)}	High - Side Bias Voltage Ground for V Phase IGBT Driving
24	V _{B(V)}	High - Side Bias Voltage for V Phase IGBT Driving
25	V _{S(U)}	High - Side Bias Voltage Ground for U Phase IGBT Driving
26	V _{B(U)}	High - Side Bias Voltage for U Phase IGBT Driving

Internal Equivalent Circuit and Input/Output Pins



Note

- 1) Inverter high side is composed of three IGBTs, freewheeling diodes and one control IC for each IGBT.
- 2) Inverter low side is composed of three IGBTs, freewheeling diodes and one control IC for each IGBT. It has gate drive and protection functions.
- 3) Inverter power side is composed of four inverter dc link input terminals and three inverter output terminals.

Figure 3.

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Inverter Part

Symbol	Parameter	Conditions	Rating	Unit
V _{PN}	Supply Voltage	Applied between P - N _U , N _V , N _W	450	V
V _{PN(Surge)}	Supply Voltage (Surge)	Applied between P - N _U , N _V , N _W	500	V
V _{CES}	Collector - Emitter Voltage		600	V
± I _C	Each IGBT Collector Current	$T_{C} = 25^{\circ}C, T_{J} < 150^{\circ}C$	10	Α
± I _{CP}	Each IGBT Collector Current (Peak)	$T_C = 25^{\circ}C$, $T_J < 150^{\circ}C$, Under 1 ms Pulse Width	20	А
P _C	Collector Dissipation	T _C = 25°C per One Chip	34	W
T _J	Operating Junction Temperature	(Note 1)	- 40 ~ 150	°C

Note

Control Part

Symbol	Parameter	Conditions	Rating	Unit
V _{CC}	Control Supply Voltage	Applied between V _{CC(H)} , V _{CC(L)} - COM	20	V
V _{BS}	High - Side Control Bias Voltage	$ \begin{array}{c} \text{Applied between V}_{B(U)} \text{ - V}_{S(U)}, \text{ V}_{B(V)} \text{ - V}_{S(V)}, \\ \text{V}_{B(W)} \text{ - V}_{S(W)} \end{array} $	20	٧
V _{IN}	Input Signal Voltage	$\begin{array}{ccccc} \text{Applied between} & \text{IN}_{(\text{UH})}, & \text{IN}_{(\text{VH})}, & \text{IN}_{(\text{WH})}, \\ \text{IN}_{(\text{UL})}, & \text{IN}_{(\text{VL})}, & \text{IN}_{(\text{WL})} & \text{COM} \end{array}$	- 0.3 ~ V _{CC} + 0.3	V
V _{FO}	Fault Output Supply Voltage	Applied between V _{FO} - COM	- 0.3 ~ V _{CC} + 0.3	V
I _{FO}	Fault Output Current	Sink Current at V _{FO} pin	1	mA
V_{SC}	Current Sensing Input Voltage	Applied between C _{SC} - COM	- 0.3 ~ V _{CC} + 0.3	>

Bootstrap Diode Part

Symbol	Parameter	Conditions	Rating	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage		600	V
I _F	Forward Current	$T_{C} = 25^{\circ}C, T_{J} < 150^{\circ}C$	0.50	Α
I _{FP}	Forward Current (Peak)	T_{C} = 25°C, T_{J} < 150°C, Under 1 ms Pulse Width	1.50	Α
T _J	Operating Junction Temperature		- 40 ~ 150	°C

Total System

Symbol	Parameter	Conditions	Rating	Unit
V _{PN(PROT)}	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}$ T _J = 150°C, Non - repetitive, less than 2 μs	400	V
T _{STG}	Storage Temperature		- 40 ~ 125	°C
V _{ISO}	Isolation Voltage	60 Hz, Sinusoidal, AC 1 minute, Connection pins to heat sink plate	2000	V _{rms}

Thermal Resistance

Syn	nbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
R _{th}	ı(j-c)Q	Junction to Case Thermal Resistance	Inverter IGBT part (per 1 / 6 module)	-	-	3.6	°C/W
R _{th}	n(j-c)F		Inverter FWD part (per 1 / 6 module)	-	-	4.8	°C/W

^{1.} The maximum junction temperature rating of the power chips integrated within the Motion SPM 8 45 product is 150°C.

^{2.} For the measurement point of case temperature ($T_{\mbox{\scriptsize C}}$), please refer to Figure 2.

Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Inverter Part

S	ymbol	Parameter	Cond	itions	Min.	Тур.	Max.	Unit
V	V _{CE(SAT)} Collector - Emitter S Voltage		$V_{CC} = V_{BS} = 15 \text{ V}$ $V_{IN} = 5 \text{ V}$	I _C = 10 A, T _J = 25°C	-	1.7	2.2	V
	V _F	FWD Forward Voltage	V _{IN} = 0 V	I _F = 10 A, T _J = 25°C	-	1.8	2.3	V
HS	t _{ON}	Switching Times		$V_{PN} = 300 \text{ V}, V_{CC} = V_{BS} = 15 \text{ V}, I_C = 10 \text{ A}$ $T_J = 25^{\circ}\text{C}$ $V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}, \text{ Inductive load}$ (Note 3)		0.70	1.20	μS
	t _{C(ON)}					0.20	0.45	μS
	t _{OFF}					0.75	1.25	μS
	t _{C(OFF)}					0.25	0.50	μS
	t _{rr}				-	0.15	-	μS
LS	t _{ON}		$V_{PN} = 300 \text{ V}, V_{CC} = V_{E}$	_{3S} = 15 V, I _C = 10 A	0.40	0.70	1.20	μS
	t _{C(ON)}		$T_J = 25^{\circ}C$ $V_{IN} = 0 V \leftrightarrow 5 V$, Induc	tive load	-	0.20	0.45	μS
	t _{OFF}		(Note 3)	Silve load	-	0.75	1.25	μS
	t _{C(OFF)}			`		0.25	0.50	μS
	t _{rr}				-	0.15	-	μS
	I _{CES}	Collector - Emitter Leakage Current	V _{CE} = V _{CES}		-	-	1	mA

Note

^{3.} t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

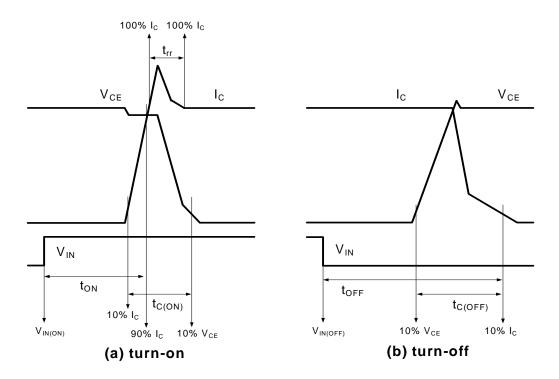


Figure 4. Switching Time Definition

Switching Loss (Typical)

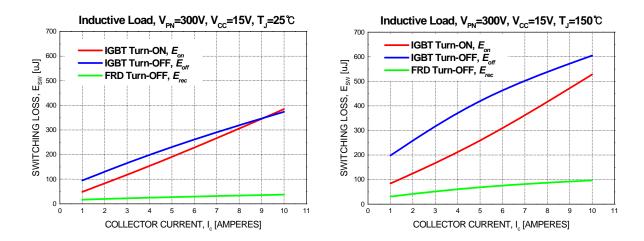


Figure 5. Switching Loss Characteristics

Control Part

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
I _{QCCH}	Quiescent V _{CC} Supply	V _{CC(H)} = 15 V, IN _(UH,VH,WH) = 0 V	V _{CC(H)} - COM	-	-	0.10	mA
I _{QCCL}	Current	$V_{CC(L)} = 15 \text{ V}, \text{ IN}_{(UL,VL, WL)} = 0 \text{ V} \text{ V}_{CC(L)} - \text{COM}$		-	-	2.65	mA
I _{PCCH}	Operating V _{CC} Supply Current	$V_{\rm CC(H)}$ = 15 V, $f_{\rm PWM}$ = 20 kHz, duty = 50%, applied to one PWM signal input for high - side	V _{CC(H)} - COM	-	-	0.15	mA
I _{PCCL}		$V_{\text{CC(L)}}$ = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for low - side	V _{CC(L)} - COM	1	-	3.65	mA
I _{QBS}	Quiescent V _{BS} Supply Current	V _{BS} = 15 V, IN _(UH, VH, WH) = 0 V	$V_{B(U)} - V_{S(U)}, V_{B(V)} - V_{S(V)}, V_{B(W)} - V_{S(W)}$	1	-	0.30	mA
I _{PBS}	Operating V _{BS} Supply Current	$V_{CC} = V_{BS} = 15 \text{ V}, f_{PWM} = 20 \text{ kHz},$ duty = 50%, applied to one PWM signal input for high - side	$V_{B(U)} - V_{S(U)}, V_{B(V)} - V_{S(V)}, V_{B(W)} - V_{S(W)}$	-	-	2.00	mA
V_{FOH}	Fault Output Voltage	$V_{SC} = 0 \text{ V}, V_{FO} \text{ Circuit: } 10 \text{ k}\Omega \text{ to } 5 \text{ V}$	/ Pull - up	4.5	-	-	V
V_{FOL}		V_{SC} = 1 V, V_{FO} Circuit: 10 k Ω to 5 V	/ Pull - up	-	-	0.5	V
V _{SC(ref)}	Short Circuit Trip Level	V _{CC} = 15 V (Note 4)		0.45	0.5	0.55	V
UV _{CCD}		Detection level		10.5	-	13.0	V
UV _{CCR}	Supply Circuit Under - Voltage	Reset level		11.0	-	13.5	V
UV _{BSD}	Protection	Detection level		10.0	-	12.5	V
UV _{BSR}		Reset level		10.5	-	13.0	V
t _{FOD}	Fault - Out Pulse Width			30	-	-	μS
V _{IN(ON)}	ON Threshold Voltage	Applied between IN(UH), IN(VH), II	N _(WH) , IN _(UL) , IN _(VL) ,	-	-	2.6	V
V _{IN(OFF)}	OFF Threshold Voltage	IN _(WL) - COM		0.8	-	-	V
R _{TH}	Resistance of	@T _{TH} = 25°C, (Note 5)	@T _{TH} = 25°C, (Note 5)		47	-	kΩ
	Thermister	@T _{TH} = 100°C		-	2.9	-	kΩ

^{4.} Short - circuit current protection is functioning only at the low - sides.

 $^{5.\} T_{TH}\ is\ the\ temperature\ of\ thermister\ itselt.\ To\ know\ case\ temperature\ (T_C),\ please\ make\ the\ experiment\ considering\ your\ application.$

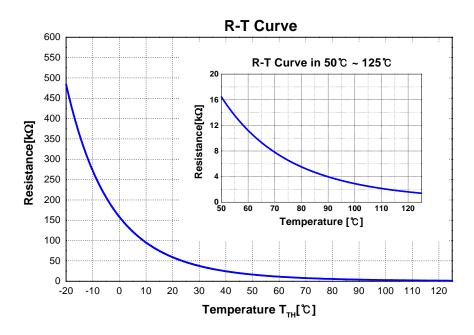
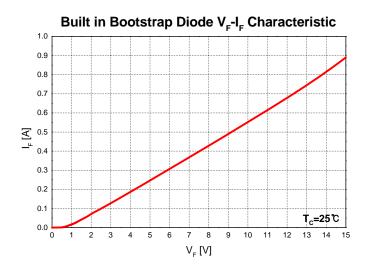


Figure. 6. R-T Curve of The Built-in Thermistor

Bootstrap Diode Part

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _F	Forward Voltage	I _F = 0.1 A, T _C = 25°C	-	2.5	-	V
t _{rr}	Reverse Recovery Time	$I_F = 0.1 \text{ A}, T_C = 25^{\circ}\text{C}$	-	80	-	ns



Note:

6. Built in bootstrap diode includes around 15 Ω resistance characteristic.

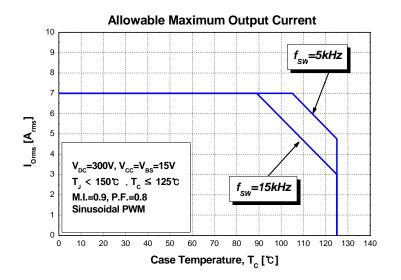
Figure 7. Built in Bootstrap Diode Characteristic

Recommended Operating Conditions

Cumbal	Doromotor	Conditions		Value		I Imi4
Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
V _{PN}	Supply Voltage	Applied between P - N _U , N _V , N _W	-	300	400	V
V _{CC}	Control Supply Voltage	Applied between V _{CC(H)} , V _{CC(L)} - COM	13.5	15	16.5	V
V_{BS}	High - Side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	13.0	15	18.5	V
dV_{CC} / dt , dV_{BS} / dt	Control Supply Variation		- 1	-	1	V/μs
t _{dead}	Blanking Time for Preventing Arm - Short	For each input signal	1.5	-	-	μS
f _{PWM}	PWM Input Signal	- 40°C < T _J < 150°C	-	-	20	kHz
V _{SEN}	Voltage for Current Sensing	Applied between N _U , N _V , N _W - COM (Including surge voltage)	- 4		4	V
P _{WIN(ON)}	Minimun Input Pulse	(Note 7)	0.5	-	-	μS
P _{WIN(OFF)}	Width		0.5	-	-	

Note:

7. This product might not make response if input pulse width is less than the recommanded value.



Note

8. This allowable output current value is the reference data for the safe operation of this product. The allowable output current value may be different from the actual application.

Figure 8. Allowable Maximum Output Current

Mechanical Characteristics and Ratings

Parameter	C	Conditions			Limits			
Parameter					Max.	Unit		
Device Flatness	Note Figure 9		0	-	+ 120	μm		
Mounting Torque	Mounting Screw: - M3	Recommended 0.7 N • m	0.6	0.7	0.8	N • m		
	Note Figure 10	Recommended 7.1 kg • cm	6.2	7.1	8.1	kg • cm		
Weight		•	-	11	-	g		

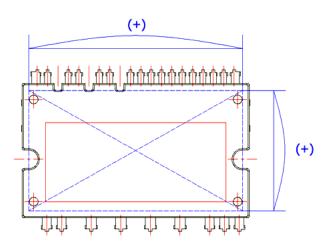


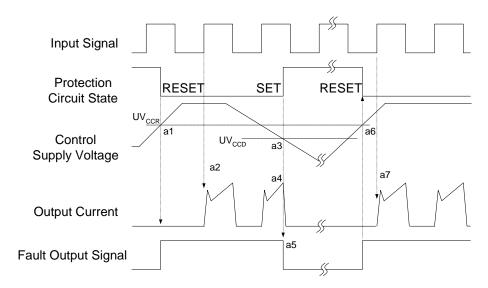
Figure 9. Flatness Measurement Position

Pre - Screwing : 1→2
Final Screwing : 2→1

- 9. Do not make over torque when mounting screws. Much mounting torque may cause ceramic cracks, as well as bolts and Al heat sink destruction.
- 10. Avoid one side tightening stress. Figure 10 shows the recommended torque order for mounting screws. Uneven mounting can cause the ceramic substrate of the Motion SPM® 45 product to be damaged. The Pre Screwing torque is set to 20 ~ 30% of maximum torque rating.

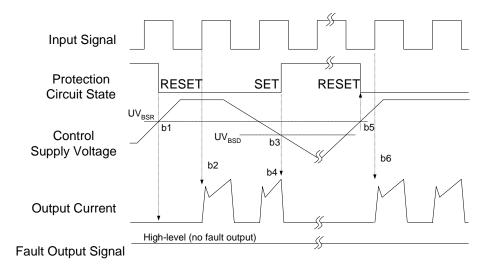
Figure 10. Mounting Screws Torque Order

Time Charts of Protective Function



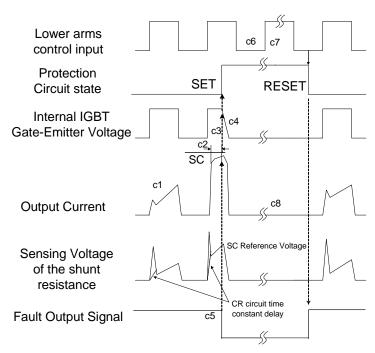
- a1 : Control supply voltage rises: After the voltage rises UV_{CCR}, the circuits start to operate when next input is applied.
- a2: Normal operation: IGBT ON and carrying current.
- a3 : Under voltage detection (UV_{CCD}).
- a4: IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under voltage reset (UV $_{CCR}$).
- a7: Normal operation: IGBT ON and carrying current.

Figure 11. Under - Voltage Protection (Low - Side)



- b1 : Control supply voltage rises: After the voltage reaches UV_{BSR}, the circuits start to operate when next input is applied.
- b2: Normal operation: IGBT ON and carrying current.
- b3 : Under voltage detection (UV_{BSD}).
- b4: IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under voltage reset (UV_{BSR})
- b6: Normal operation: IGBT ON and carrying current

Figure 12. Under - Voltage Protection (High - Side)

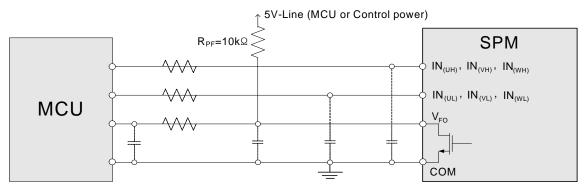


(with the external shunt resistance and CR connection)

- c1: Normal operation: IGBT ON and carrying current.
- c2 : Short circuit current detection (SC trigger).
- c3: Hard IGBT gate interrupt.
- c4: IGBT turns OFF.
- c5 : Input "L" : IGBT OFF state.
- c6 : Input "H": IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.
- c7: IGBT OFF state

Figure 13. Short - Circuit Current Protection (Low - Side Operation only)

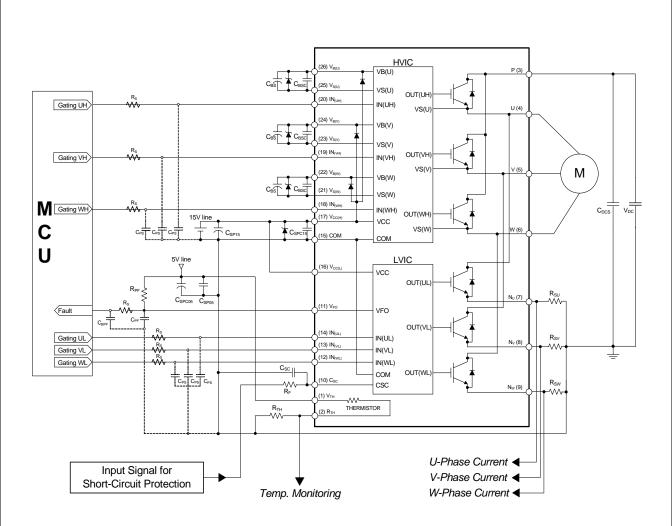
Input/Output Interface Circuit



Note

- 1) RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the Motion SPM[®] 45 product integrates 5 kΩ (typ.) pull down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.
- 2) The logic input is compatible with standard CMOS outputs.

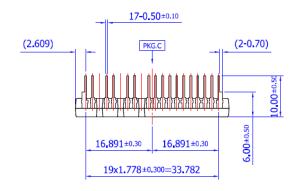
Figure 14. Recommended CPU I/O Interface Circuit

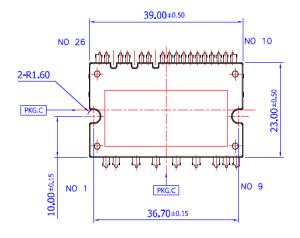


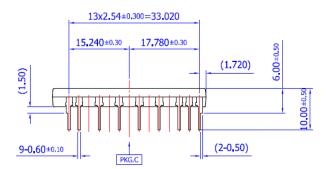
- 1) To avoid malfunction, the wiring of each input should be as short as possible. (less than 2 3 cm)
- 2) By virtue of integrating an application specific type HVIC inside the Motion SPM® 45 product, direct coupling to CPU terminals without any opto coupler or transformer isolation is possible.
- 3) V_{FO} output is open drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I_{FO} up to 1 mA. Please refer to Figure 14.
- 4) C_{SP15} of around 7 times larger than bootstrap capacitor C_{BS} is recommended.
- 5) Input signal is High Active type. There is a 5 k Ω resistor inside the IC to pull down each input signal line to GND. RC coupling circuits is recommanded for the prevention of input signal oscillation. R_SC_{PS} time constant should be selected in the range 50 ~ 150 ns. (Recommended R_S = 100 Ω , C_{PS} = 1 nF)
- 6) To prevent errors of the protection function, the wiring around R_F and C_{SC} should be as short as possible.
- 7) In the short circuit protection circuit, please select the $R_F C_{SC}$ time constant in the range 1.5 ~ 2 μs .
- 8) Each capacitor should be mounted as close to the pins of the SPM as possible.
- 9) To prevent surge destruction, the wiring between the smoothing capacitor and the P & GND pins should be as short as possible. The use of a high frequency non inductive capacitor of around 0.1 ~ 0.22 µF between the P & GND pins is recommended.
- 10) Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.
- 11) The zener diode should be adopted for the protection of ICs from the surge destruction between each pair of control supply terminals. (Recommanded zener diode = 22 V / 1 W)
- 12) Please choose the electrolytic capacitor with good temperature characteristic in C_{BS} . Also, choose 0.1 ~ 0.2 μF R category ceramic capacitors with good temperature and frequency characteristics in C_{BSC} .
- 13) For the detailed information, please refer to the AN 9070, AN 9071, AN 9072, RD 344, and RD 345.

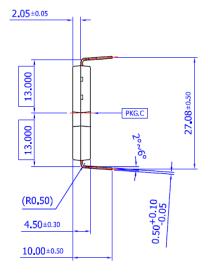
Figure 15. Typical Application Circuit

Detailed Package Outline Drawings (FNA41060)

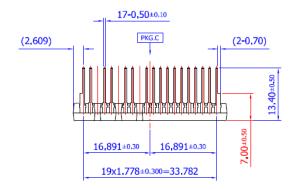


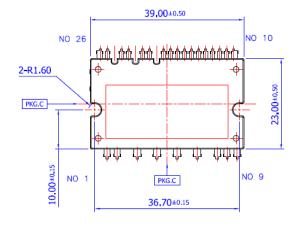


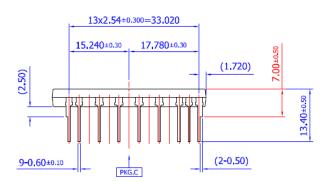


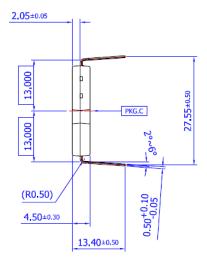


Detailed Package Outline Drawings (FNA41060B2, Long Terminal Type)













TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

 $\begin{array}{lll} 2 Cool^{\text{TM}} & & \text{FPS}^{\text{TM}} \\ \text{AccuPower}^{\text{TM}} & & \text{F-PFS}^{\text{TM}} \\ \text{AX-CAP}^{\otimes_*} & & \text{FRFET}^{\otimes} \end{array}$

BitSiC™ Global Power ResourceSM
Build it Now™ GreenBridge™

 $\begin{array}{lll} {\sf CorePLUS^{\rm TM}} & {\sf Green} \; {\sf FPS^{\rm TM}} \\ {\sf CorePOWER^{\rm TM}} & {\sf Green} \; {\sf FPS^{\rm TM}} \; {\sf e-Series^{\rm TM}} \end{array}$

 CROSSVOLT™
 Gmax™

 CTL™
 GTO™

 Current Transfer Logic™
 IntelliMAX™

 DEUXPEED®
 ISOPLANAR™

Dual Cool™ Making Small Speakers Sound Louder

EcoSPARK[®] and Better™
EfficientMax™ MegaBuck™

Fairchild® MicroPak™

Fairchild Semiconductor®
FACT Quiet Series™ MotionMax™
FACT® MotionMax™
FAST® MWSaver™

FastvCore™ OptoHiT™
OPTOLOGIC®
FETBench™ OPTOPLANAR®

®
PowerTrench®
PowerXS™

Programmable Active Droop™ QFET[®]

QSTM
Quiet SeriesTM
RapidConfigureTM

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-8
SuperSOT™-8
SupreMOS®
SyncFET™

Sync-Lock™

SYSTEM

GENERAL®*

TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPOWer™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
uSerDes™

SerDes"
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 164

^{*} Trademarks of System General Corporation, used under license by Fairchild Semiconductor.